

RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

Designed for N-CDMA base station applications with frequencies from 1930 to 1990 MHz. Suitable for TDMA, CDMA and multicarrier amplifier applications. To be used in Class AB for PCN - PCS/cellular radio and WLL applications.

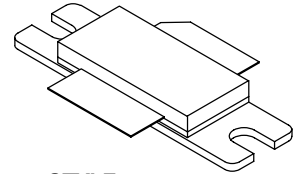
- Typical 2-Carrier N-CDMA Performance: $V_{DD} = 28$ Volts, $I_{DQ} = 900$ mA, $P_{out} = 22$ Watts Avg., $f = 1987$ MHz, IS-95 (Pilot, Sync, Paging, Traffic Codes 8 Through 13) Channel Bandwidth = 1.2288 MHz. PAR = 9.8 dB @ 0.01% Probability on CCDF.
Power Gain — 16.1 dB
Drain Efficiency — 28%
IM3 @ 2.5 MHz Offset — -37 dBc in 1.2288 MHz Channel Bandwidth
ACPR @ 885 kHz Offset — -51 dBc in 30 kHz Channel Bandwidth
- Capable of Handling 10:1 VSWR, @ 28 Vdc, 1960 MHz, 100 Watts CW Output Power

Features

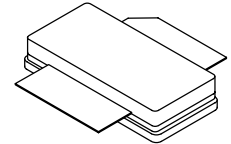
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Qualified Up to a Maximum of 32 V_{DD} Operation
- Integrated ESD Protection
- Designed for Lower Memory Effects and Wide Instantaneous Bandwidth Applications
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.

MRF6S19100HR3
MRF6S19100HSR3

1930-1990 MHz, 22 W AVG., 28 V
2 x N-CDMA
LATERAL N-CHANNEL
RF POWER MOSFETs



CASE 465-06, STYLE 1
NI-780
MRF6S19100HR3



CASE 465A-06, STYLE 1
NI-780S
MRF6S19100HSR3

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +68	Vdc
Gate-Source Voltage	V_{GS}	-0.5, +12	Vdc
Storage Temperature Range	T_{stg}	- 65 to +150	°C
Case Operating Temperature	T_C	150	°C
Operating Junction Temperature (1,2)	T_J	225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (2,3)	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.44	°C/W
Case Temperature 80°C, 100 W CW		0.50	
Case Temperature 77°C, 22 W CW			

1. Continuous use at maximum temperature will affect MTTF.
2. MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	3A (Minimum)
Machine Model (per EIA/JESD22-A115)	B (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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Off Characteristics

Zero Gate Voltage Drain Leakage Current ($V_{DS} = 68\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc

On Characteristics

Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 250\text{ }\mu\text{Adc}$)	$V_{GS(th)}$	1	2	3	Vdc
Gate Quiescent Voltage ($V_{DD} = 28\text{ Vdc}$, $I_D = 900\text{ mAdc}$, Measured in Functional Test)	$V_{GS(Q)}$	2	2.8	4	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 2.2\text{ Adc}$)	$V_{DS(on)}$	0.1	0.21	0.3	Vdc

Dynamic Characteristics ⁽¹⁾

Reverse Transfer Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	1.5	—	pF
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Functional Tests (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 900\text{ mA}$, $P_{out} = 22\text{ W Avg.}$, $f = 1987\text{ MHz}$, 2-carrier N-CDMA, 1.2288 MHz Channel Bandwidth Carriers. ACPR measured in 30 kHz Channel Bandwidth @ $\pm 885\text{ kHz}$ Offset. IM3 measured in 1.2288 MHz Channel Bandwidth @ $\pm 2.5\text{ MHz}$ Offset. PAR = 9.8 dB @ 0.01% Probability on CCDF.

Power Gain	G_{ps}	15	16.1	18	dB
Drain Efficiency	η_D	26	28	—	%
Intermodulation Distortion	IM3	—	-37	-35	dBc
Adjacent Channel Power Ratio	ACPR	—	-51	-48	dBc
Input Return Loss	IRL	—	-15	-9	dB

1. Part is internally matched both on input and output.

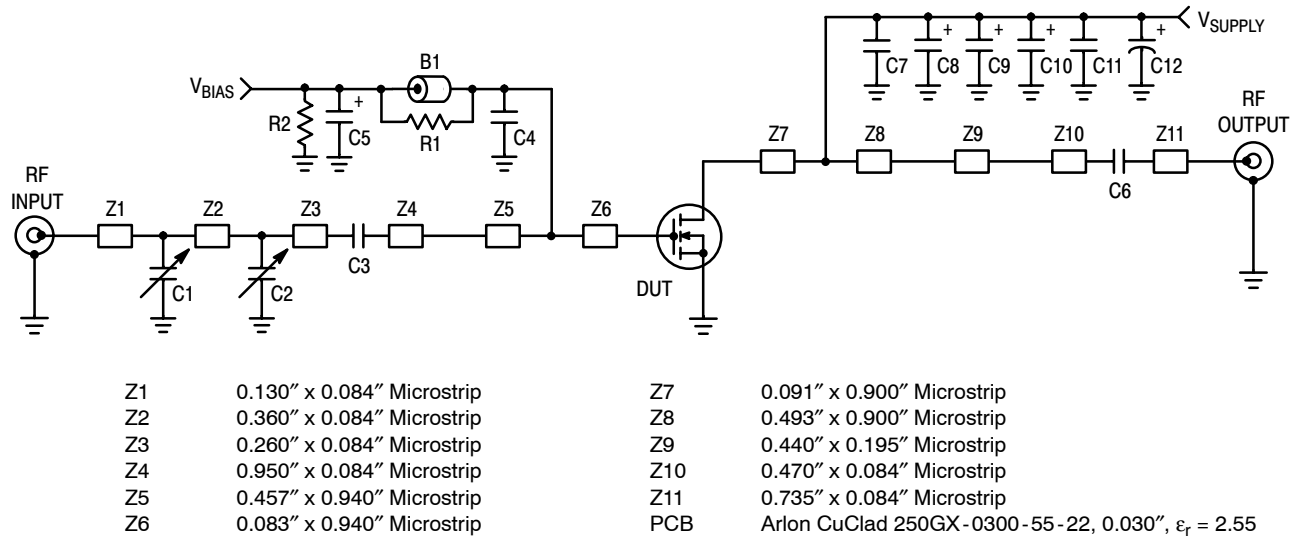
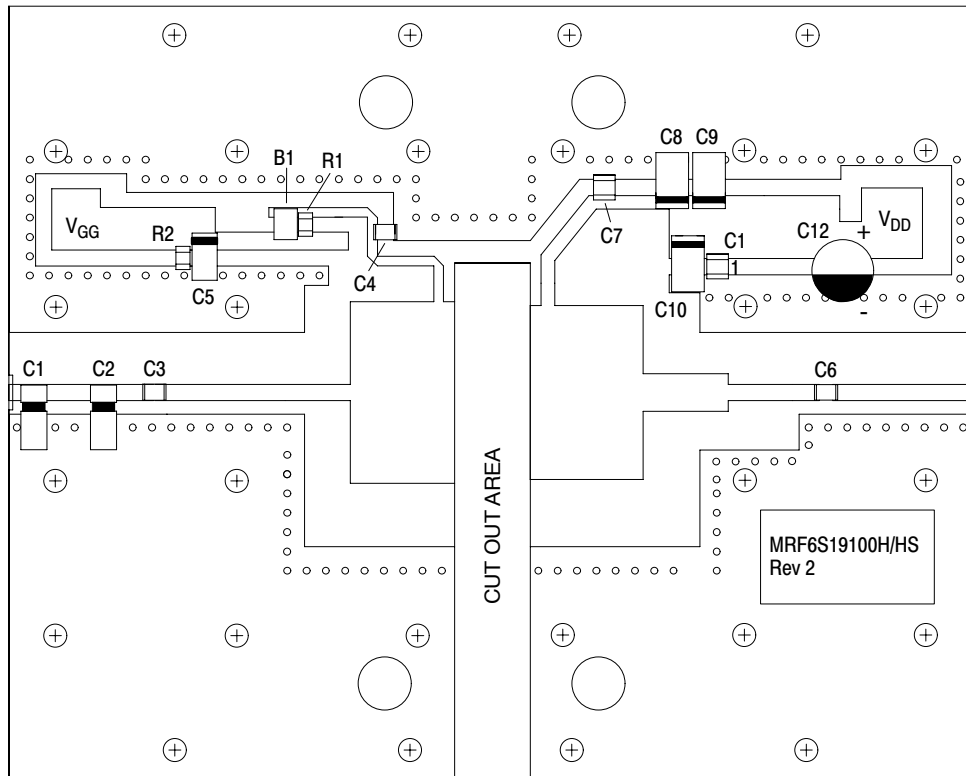


Figure 1. MRF6S19100HR3(HSR3) Test Circuit Schematic

Table 5. MRF6S19100HR3(HSR3) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
B1	RF Bead	2743019447	Fair-Rite
C1, C2	0.6 - 4.5 pF Variable Capacitors, Gigatronics	27271SL	Johanson Dielectrics
C3	15 pF Chip Capacitor	ATC100B150CT500XT	ATC
C4, C7	5.6 pF Chip Capacitors	ATC100B5R6JT500XT	ATC
C5	1 μ F, 50 V Tantalum Chip Capacitor	T491C105K050AT	Kemet
C6	43 pF Chip Capacitor	ATC100B430CT500XT	ATC
C8, C10	22 μ F, 35 V Tantalum Chip Capacitors	T491X226K035AT	Kemet
C9	10 μ F, 35 V Tantalum Chip Capacitor	T491C106K035AT	Kemet
C11	0.1 μ F Chip Capacitor	C1825C14J5RAC	Kemet
C12	100 μ F, 50 V Electrolytic Capacitor	MCHT101M1HB-1017-RH	Multicomp
R1	12 Ω , 1/4 W Chip Resistor	CRCW120612R0FKEA	Vishay
R2	2 k Ω , 1/4 W Chip Resistor	CRCW12062001FKEA	Vishay



Freescall has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescall Semiconductor signature/logo. PCBs may have either Motorola or Freescall markings during the transition period. These changes will have no impact on form, fit or function of the current product.

Figure 2. MRF6S19100HR3(HSR3) Test Circuit Component Layout

TYPICAL CHARACTERISTICS

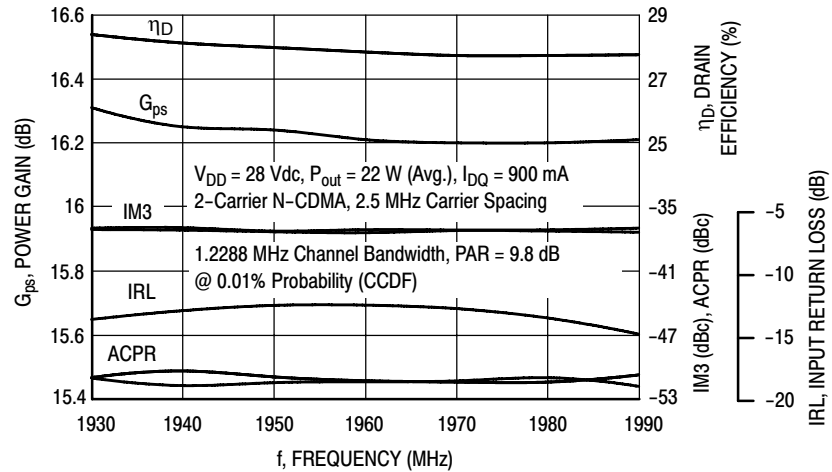


Figure 3. 2-Carrier N-CDMA Broadband Performance @ $P_{out} = 22$ Watts Avg.

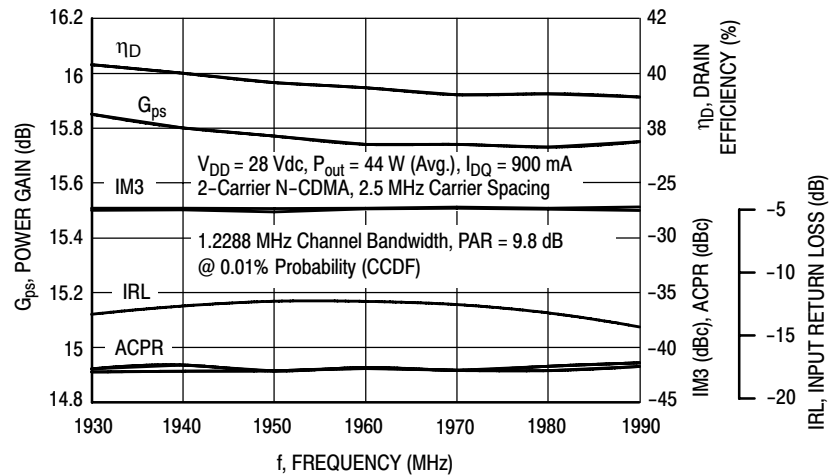


Figure 4. 2-Carrier N-CDMA Broadband Performance @ $P_{out} = 44$ Watts Avg.

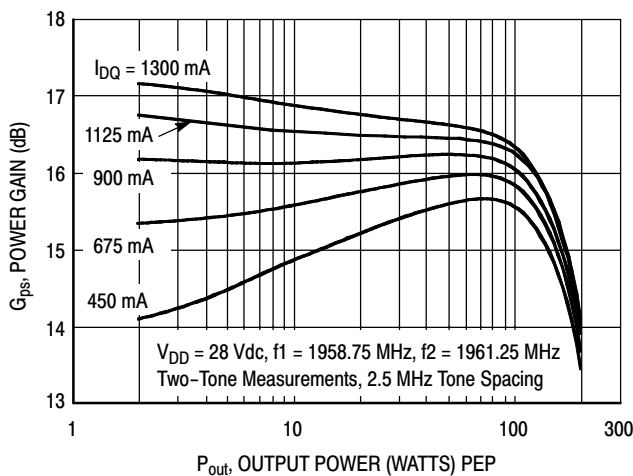


Figure 5. Two-Tone Power Gain versus Output Power

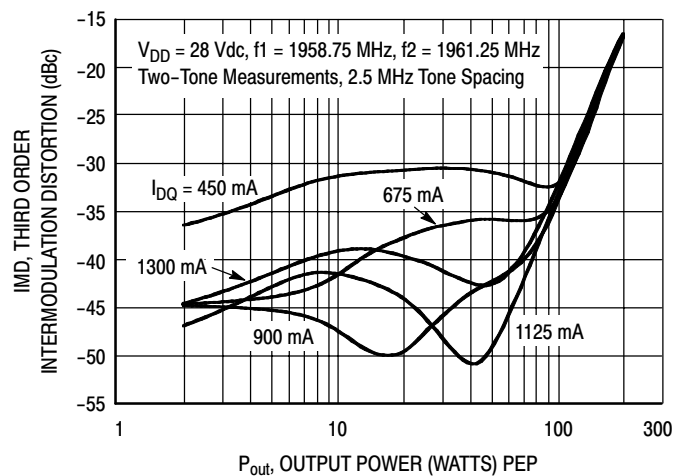


Figure 6. Third Order Intermodulation Distortion versus Output Power

TYPICAL CHARACTERISTICS

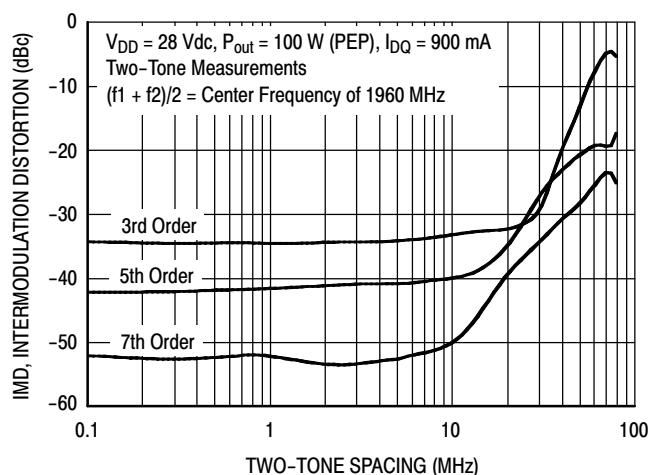


Figure 7. Intermodulation Distortion Products versus Tone Spacing

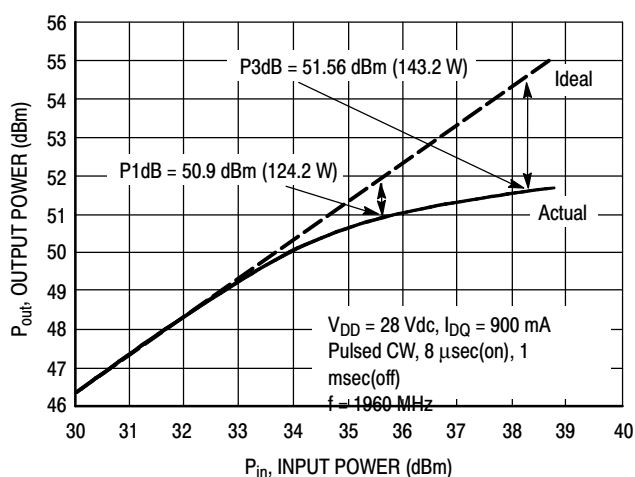


Figure 8. Pulsed CW Output Power versus Input Power

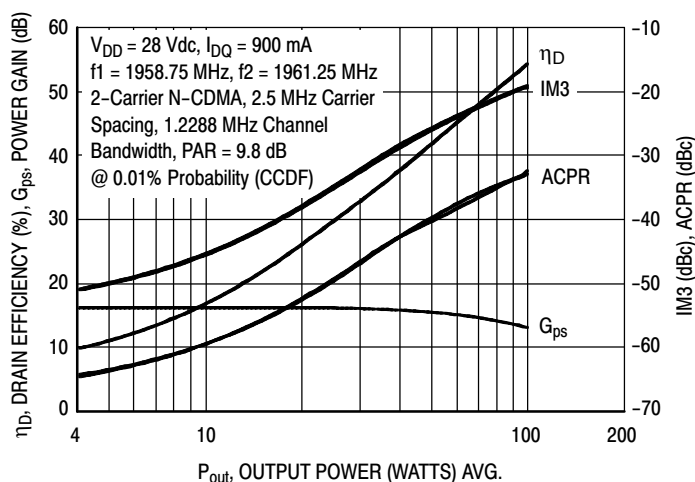


Figure 9. 2-Carrier N-CDMA ACPR, IM3, Power Gain and Drain Efficiency versus Output Power

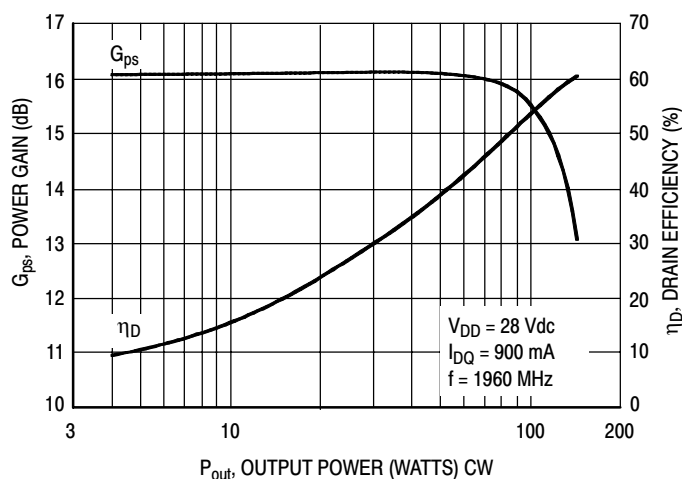


Figure 10. Power Gain and Drain Efficiency versus CW Output Power

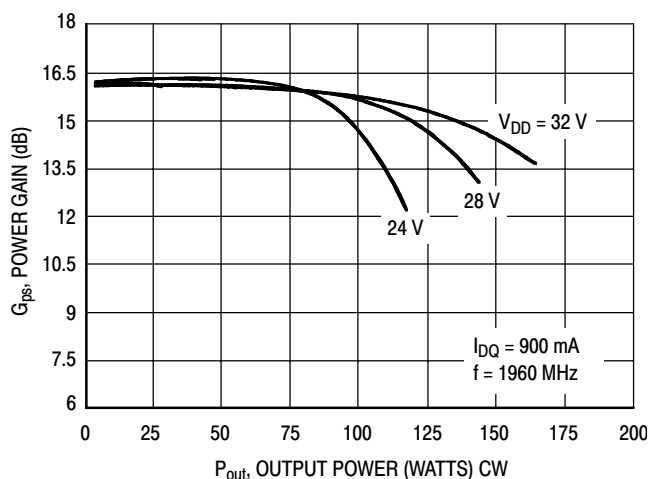
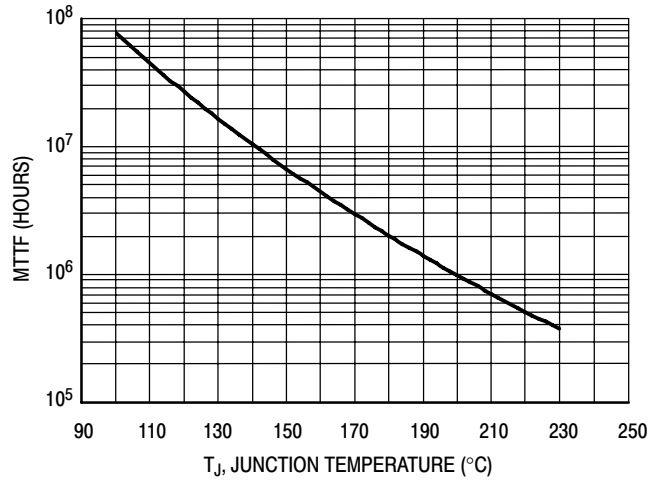


Figure 11. Power Gain versus Output Power

TYPICAL CHARACTERISTICS



This above graph displays calculated MTTF in hours when the device is operated at $V_{DD} = 28$ Vdc, $P_{out} = 22$ W Avg., and $\eta_D = 28\%$.

MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.

Figure 12. MTTF Factor versus Junction Temperature

N-CDMA TEST SIGNAL

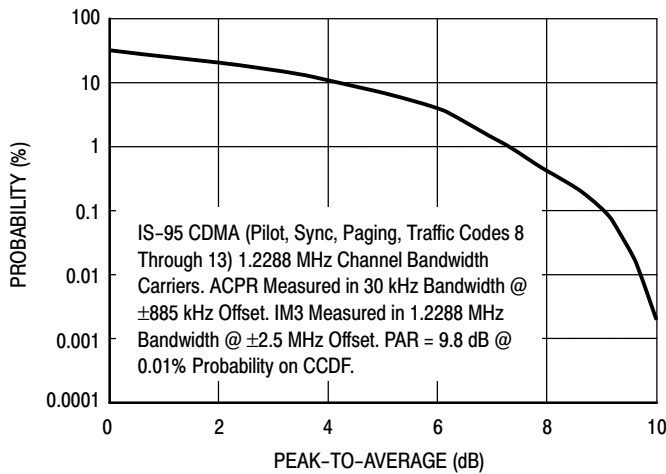


Figure 13. 2-Carrier CCDF N-CDMA

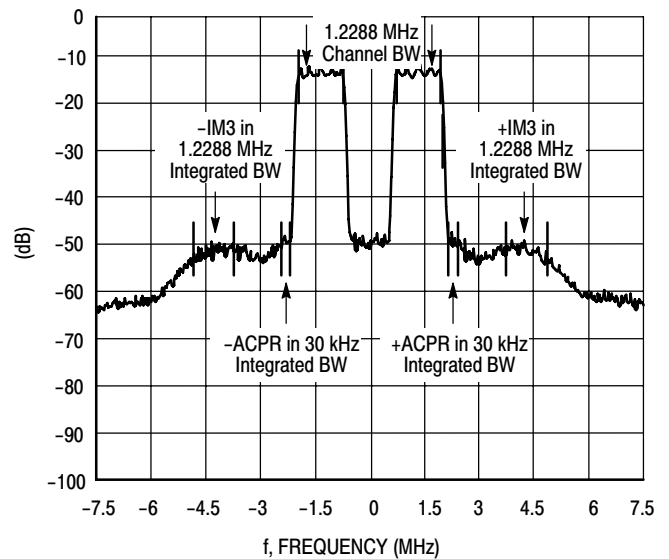
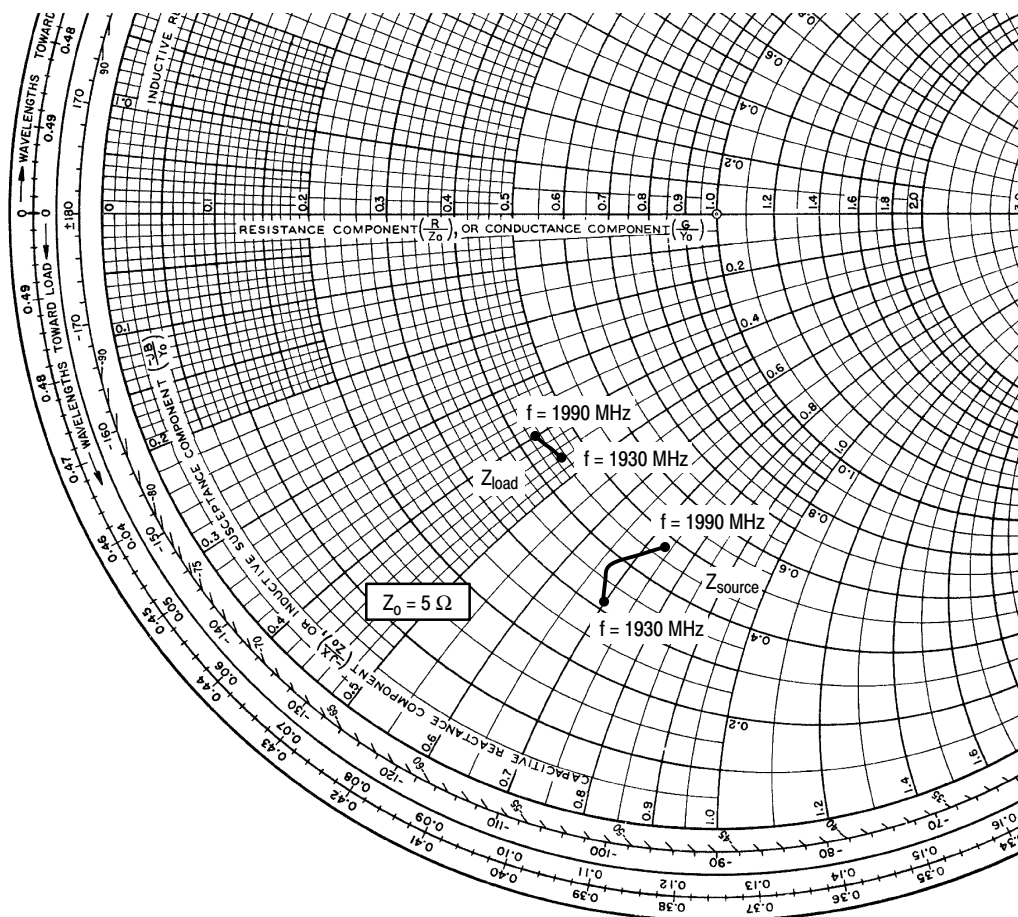


Figure 14. 2-Carrier N-CDMA Spectrum



$V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 900 \text{ mA}$, $P_{out} = 22 \text{ W Avg.}$

f MHz	Z_{source} Ω	Z_{load} Ω
1930	$1.57 - j3.50$	$2.26 - j2.31$
1960	$1.83 - j3.29$	$2.22 - j2.13$
1990	$2.34 - j3.71$	$2.14 - j2.00$

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

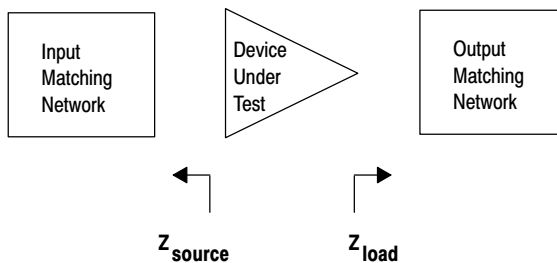
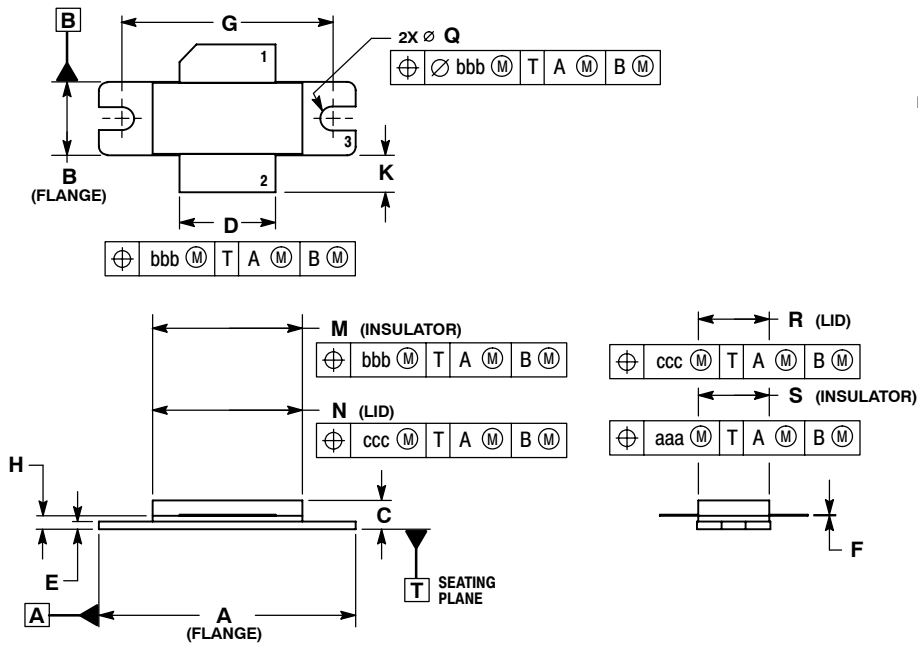


Figure 15. Series Equivalent Source and Load Impedance

PACKAGE DIMENSIONS



NOTES:

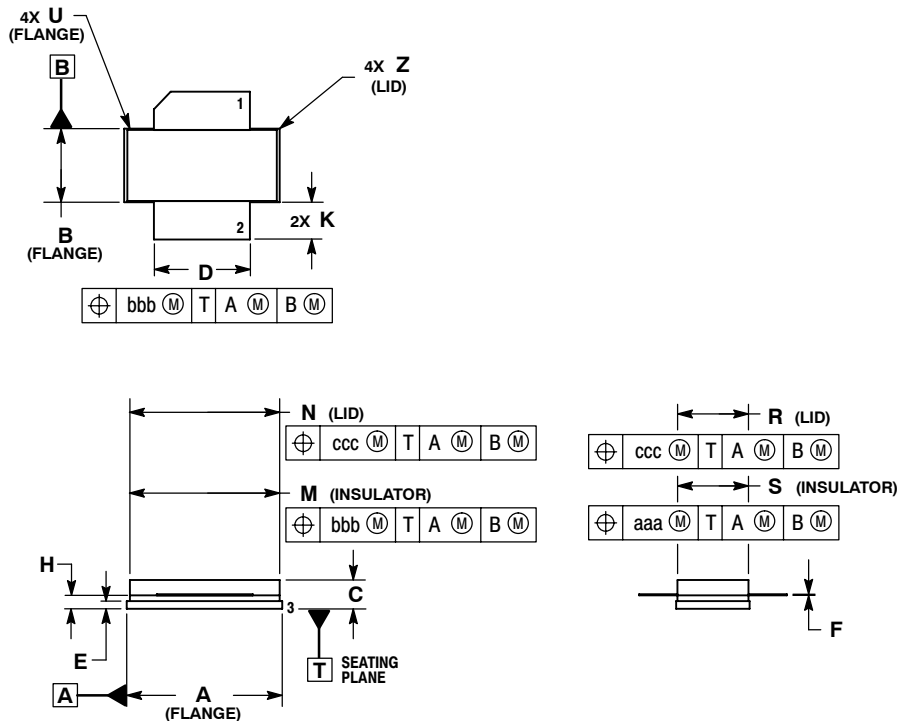
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DELETED
4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
G	1.100 BSC		27.94 BSC	
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.66	19.96
N	0.772	0.788	19.60	20.00
Q	Ø.118	Ø.138	Ø.300	Ø.351
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:

- PIN 1. DRAIN
- GATE
- SOURCE

**CASE 465-06
ISSUE G
NI-780
MRF6S19100HR3**



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
3. DELETED
4. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.805	0.815	20.45	20.70
B	0.380	0.390	9.65	9.91
C	0.125	0.170	3.18	4.32
D	0.495	0.505	12.57	12.83
E	0.035	0.045	0.89	1.14
F	0.003	0.006	0.08	0.15
H	0.057	0.067	1.45	1.70
K	0.170	0.210	4.32	5.33
M	0.774	0.786	19.61	20.02
N	0.772	0.788	19.61	20.02
R	0.365	0.375	9.27	9.53
S	0.365	0.375	9.27	9.52
U	---	0.040	---	1.02
Z	---	0.030	---	0.76
aaa	0.005 REF		0.127 REF	
bbb	0.010 REF		0.254 REF	
ccc	0.015 REF		0.381 REF	

STYLE 1:

- PIN 1. DRAIN
- GATE
- SOURCE

**CASE 465A-06
ISSUE H
NI-780S
MRF6S19100HSR3**

MRF6S19100HR3 MRF6S19100HSR3

PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
5	Dec. 2008	• Modified data sheet to reflect RF Test Reduction described in Product and Process Change Notification number, PCN13232, p. 1, 2 • Removed Lower Thermal Resistance and Low Gold Plating bullets from Features section as functionality is standard, p. 1 • Removed Total Device Dissipation from Max Ratings table as data was redundant (information already provided in Thermal Characteristics table), p. 1 • Operating Junction Temperature increased from 200°C to 225°C in Maximum Ratings table, related "Continuous use at maximum temperature will affect MTTF" footnote added, p. 1 • Corrected V_{DS} to V_{DD} in the RF test condition voltage callout for $V_{GS(Q)}$, and added "Measured in Functional Test", On Characteristics table, p. 2 • Removed Forward Transconductance from On Characteristics table as it no longer provided usable information, p. 2 • Updated PCB information to show more specific material details, Fig. 1, Test Circuit Schematic, p. 3 • Updated Part Numbers in Table 5, Component Designations and Values, to RoHS compliant part numbers, p. 3 • Removed lower voltage tests from Fig. 11, Power Gain versus Output Power, due to fixed tuned fixture limitations, p. 6 • Replaced Fig. 12, MTTF versus Junction Temperature with updated graph. Removed Amps² and listed operating characteristics and location of MTTF calculator for device, p. 7 • Added Product Documentation and Revision History, p. 10

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